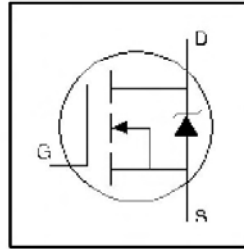


International  
**IR** Rectifier  
**HEXFET<sup>®</sup> Power MOSFET**

PD-95929

# IRFD420PbF

- Dynamic dv/dt Rating
- Repetitive Avalanche Rated
- For Automatic Insertion
- End Stackable
- Fast Switching
- Ease of paralleling
- Simple Drive Requirements
- Lead-Free

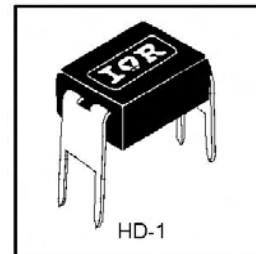


$V_{DSS} = 500V$
$R_{DS(on)} = 3.0\Omega$
$I_D = 0.37A$

### Description

Third Generation HEXFETs from International Rectifier provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

The 4-pin DIP package is a low-cost machine-insertable case style which can be stacked in multiple combinations on standard 0.1 inch pin centers. The dual drain serves as a thermal link to the mounting surface for power dissipation levels up to 1 watt.



### Absolute Maximum Ratings

	Parameter	Max.	Units
$I_D @ T_C = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10 V$	0.37	A
$I_D @ T_C = 100^\circ C$	Continuous Drain Current, $V_{GS} @ 10 V$	0.23	
$I_{DM}$	Pulsed Drain Current $\text{\textcircled{D}}$	3.0	
$P_D @ T_C = 25^\circ C$	Power Dissipation	1.0	W
	Linear Derating Factor	0.0083	W/°C
$V_{GS}$	Gate-to-Source Voltage	$\pm 20$	V
$E_{AS}$	Single Pulse Avalanche Energy $\text{\textcircled{D}}$	51	mJ
$I_{AR}$	Avalanche Current $\text{\textcircled{D}}$	0.37	A
$E_{AR}$	Repetitive Avalanche Energy $\text{\textcircled{D}}$	0.10	mJ
dv/dt	Peak Diode Recovery dv/dt $\text{\textcircled{D}}$	3.5	V/ns
$T_J$ $T_{STG}$	Operating Junction and Storage Temperature Range	-55 to + 150	°C
	Soldering Temperature, for 10 seconds	300 (1.6mm from case)	

### Thermal Resistance

	Parameter	Min.	Typ.	Max.	Units
$R_{\theta JA}$	Junction-to-Ambient	—	—	120	°C/W

# IRFD420PbF

## Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	500	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.59	—	$V/^\circ\text{C}$	Reference to $25^\circ\text{C}, I_D = 1\text{mA}$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	—	3.0	$\Omega$	$V_{GS} = 10.0V, I_D = 0.22A$ ②
$V_{GS(th)}$	Gate Threshold Voltage	2.0	—	4.0	V	$V_{DS} = V_{GS}, I_D = 250\mu A$
$g_{fs}$	Forward Transconductance	1.5	—	—	S	$V_{DS} = 50V, I_D = 1.3A$
$I_{DSS}$	Drain-to-Source Leakage Current	—	—	25	$\mu A$	$V_{DS} = 500V, V_{GS} = 0V$
		—	—	250		$V_{DS} = 400V, V_{GS} = 0V, T_J = 125^\circ\text{C}$
$I_{GSS}$	Gate-to-Source Forward Leakage	—	—	100	nA	$V_{GS} = 20V$
	Gate-to-Source Reverse Leakage	—	—	-100		$V_{GS} = -20V$
$Q_g$	Total Gate Charge	—	—	24	nC	$I_D = 2.1A$
$Q_{gs}$	Gate-to-Source Charge	—	—	3.3		$V_{DS} = 400V$
$Q_{gd}$	Gate-to-Drain ("Miller") Charge	—	—	13		$V_{GS} = 10V$ ④
$t_{d(on)}$	Turn-On Delay Time	—	8.0	—	ns	$V_{DD} = 250V$
$t_r$	Rise Time	—	8.6	—		$I_D = 2.1A$
$t_{d(off)}$	Turn-Off Delay Time	—	33	—		$R_G = 18\Omega$
$t_f$	Fall Time	—	16	—		$R_D = 120\Omega$ ④
$L_D$	Internal Drain Inductance	—	4.0	—	nH	Between lead, 6mm (0.25in.) from package and center of die contact
$L_S$	Internal Source Inductance	—	6.0	—		
$C_{iss}$	Input Capacitance	—	360	—	pF	$V_{GS} = 0V$
$C_{oss}$	Output Capacitance	—	92	—		$V_{DS} = 25V$
$C_{rss}$	Reverse Transfer Capacitance	—	37	—		$f = 1.0\text{MHz}$



## Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
$I_S$	Continuous Source Current (Body Diode)	—	—	0.37	A	MOSFET symbol showing the integral reverse p-n junction diode.
$I_{SM}$	Pulsed Source Current (Body Diode) ①	—	—	5.0		
$V_{SD}$	Diode Forward Voltage	—	—	1.6	V	$T_J = 25^\circ\text{C}, I_S = 0.37A, V_{GS} = 0V$ ②
$t_{rr}$	Reverse Recovery Time	—	260	520	ns	$T_J = 25^\circ\text{C}, I_F = 2.1A$
$Q_{rr}$	Reverse Recovery Charge	—	0.70	1.4	$\mu C$	$di/dt = 100A/\mu s$ ④
$t_{on}$	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by $L_S + L_D$ )				

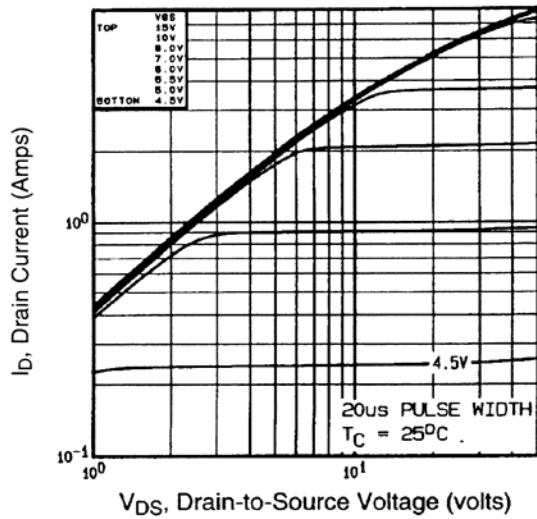
### Notes:

① Repetitive rating; pulse width limited by max. junction temperature.

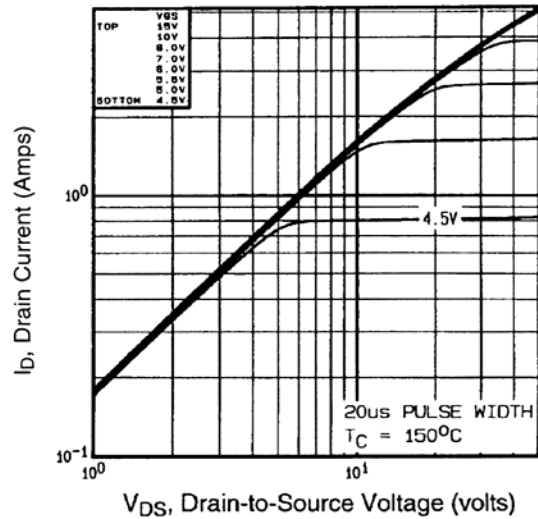
③  $I_{SD} \leq 4.4A, di/dt \leq 90A/\mu s, V_{DD} \leq V_{(BR)DSS}, T_J \leq 150^\circ\text{C}$

②  $V_{DD} = 50V, \text{starting } T_J = 25^\circ\text{C}, L = 40\text{mH}, R_G = 25\Omega, I_{AS} = 1.5A.$

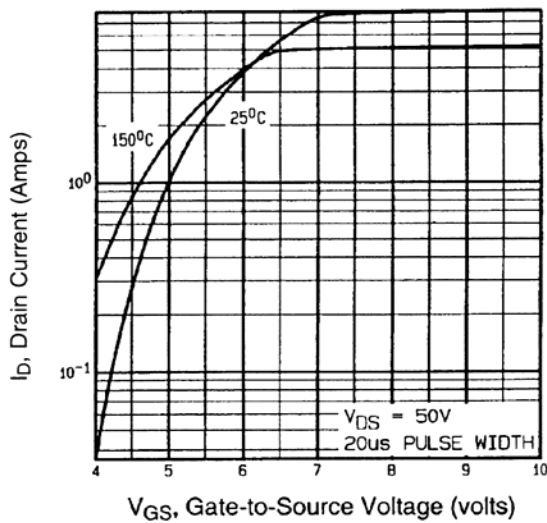
④ Pulse width  $\leq 300\mu s$ ; duty cycle  $\leq 2\%$ .



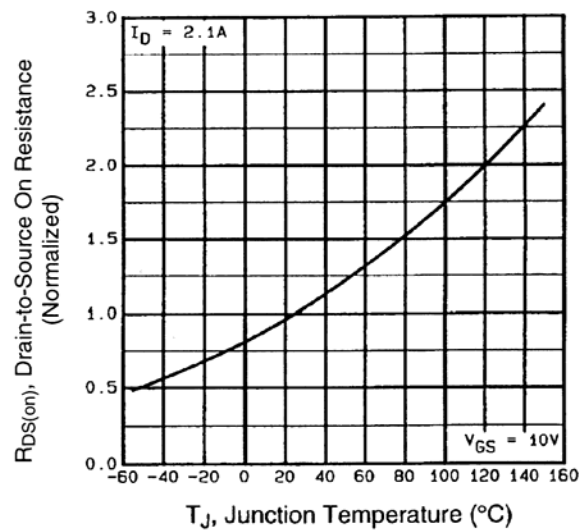
**Fig 1.** Typical Output Characteristics,  
 $T_C = 25^\circ\text{C}$



**Fig 2.** Typical Output Characteristics,  
 $T_C = 150^\circ\text{C}$

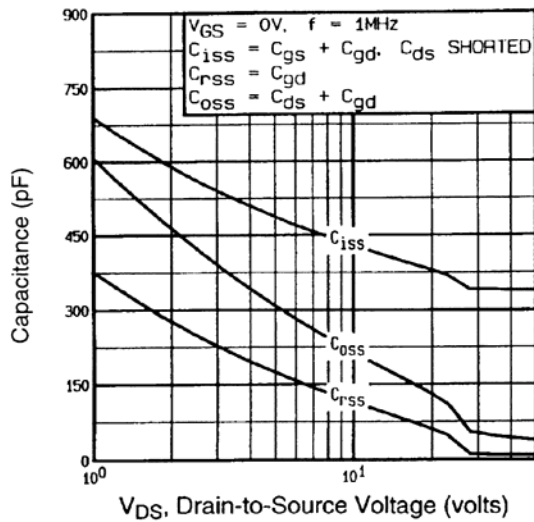


**Fig 3.** Typical Transfer Characteristics

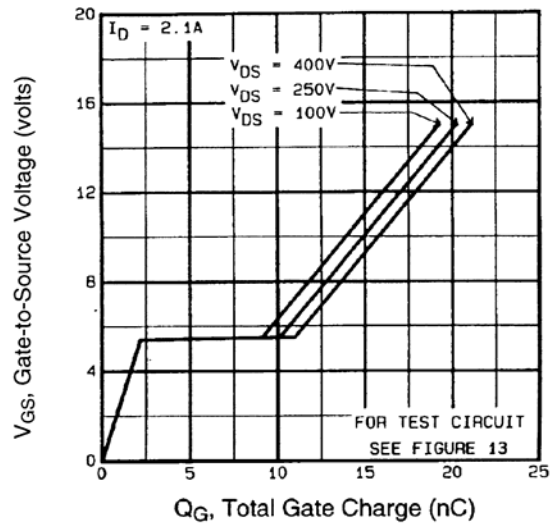


**Fig 4.** Normalized On-Resistance  
Vs. Temperature

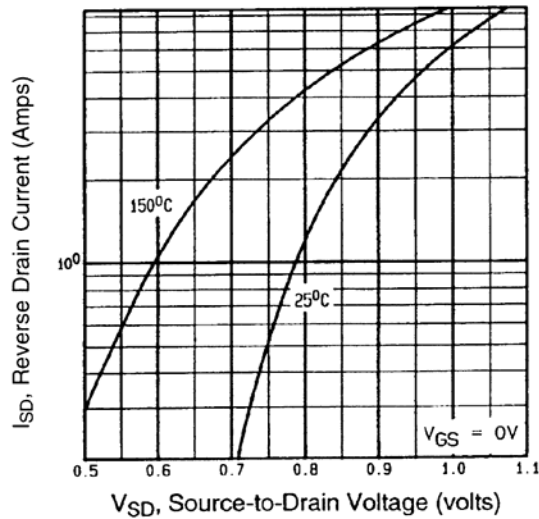
# IRFD420PbF



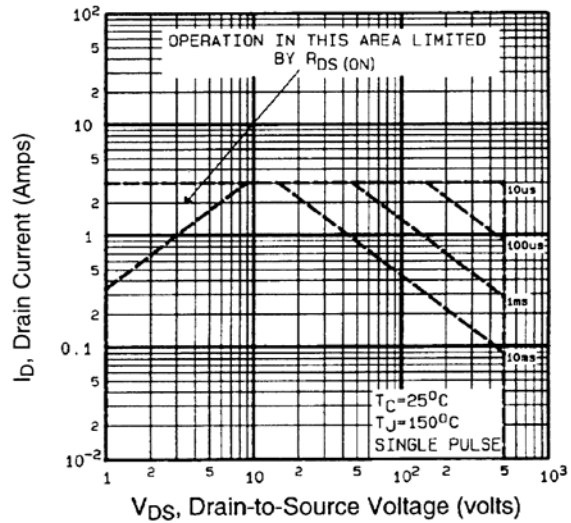
**Fig 5.** Typical Capacitance Vs. Drain-to-Source Voltage



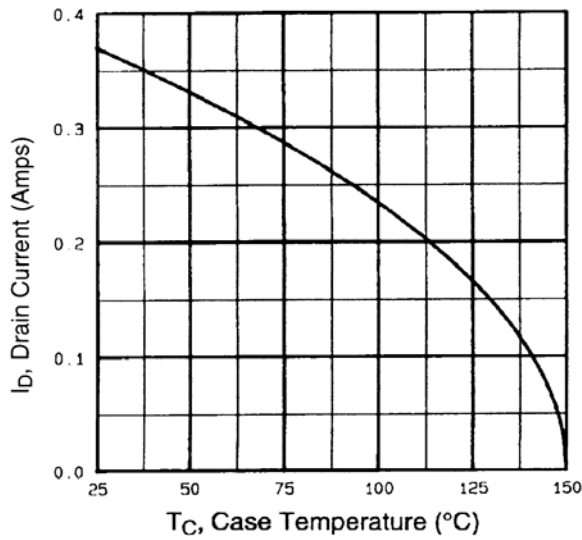
**Fig 6.** Typical Gate Charge Vs. Gate-to-Source Voltage



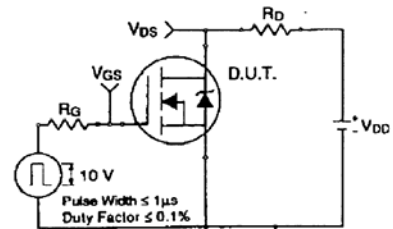
**Fig 7.** Typical Source-Drain Diode Forward Voltage



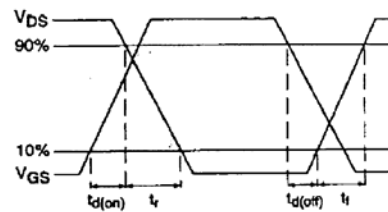
**Fig 8.** Maximum Safe Operating Area



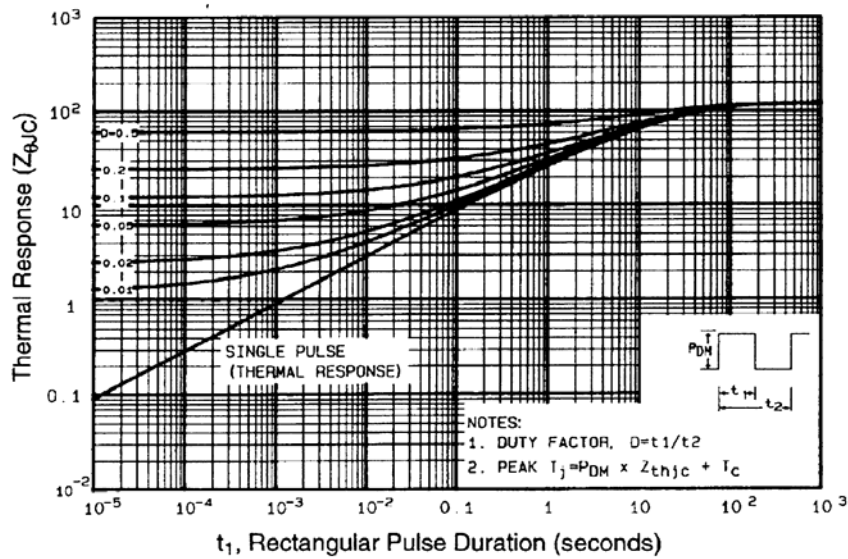
**Fig 9.** Maximum Drain Current Vs. Case Temperature



**Fig 10a.** Switching Time Test Circuit



**Fig 10b.** Switching Time Waveforms



**Fig 11.** Maximum Effective Transient Thermal Impedance, Junction-to-Case

# IRFD420PbF

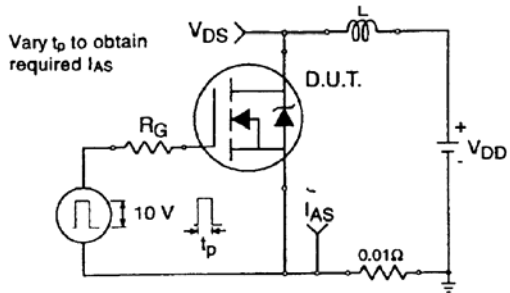


Fig 12a. Unclamped Inductive Test Circuit

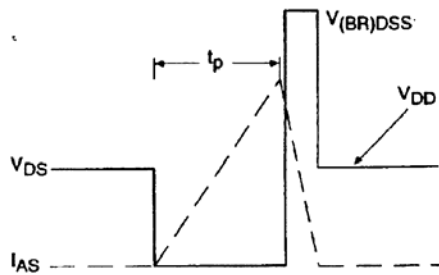


Fig 12b. Unclamped Inductive Waveforms

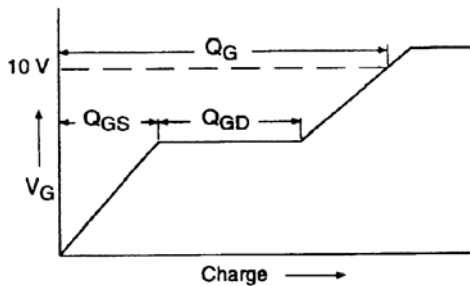


Fig 13a. Basic Gate Charge Waveform

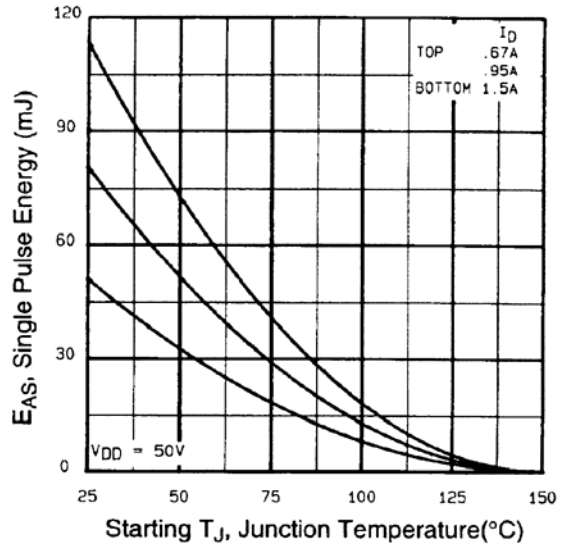


Fig 12c. Maximum Avalanche Energy Vs. Drain Current

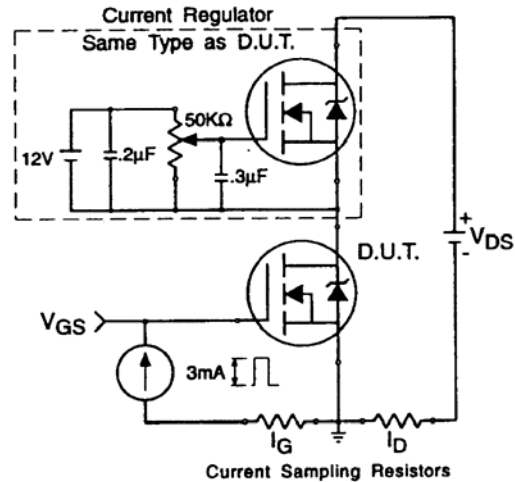
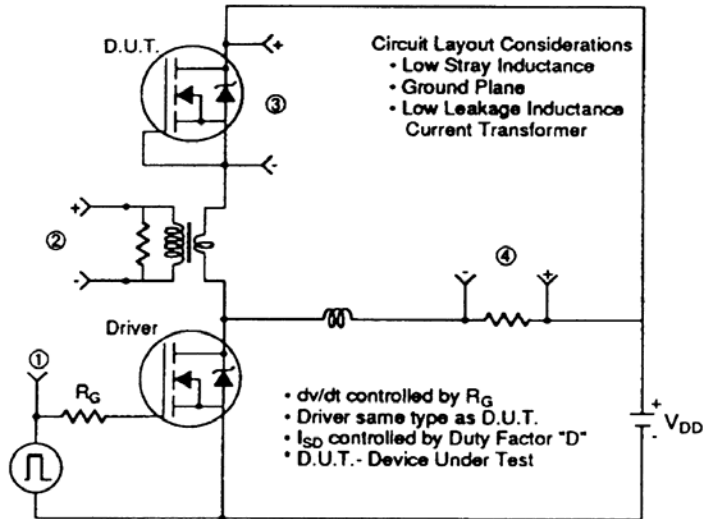


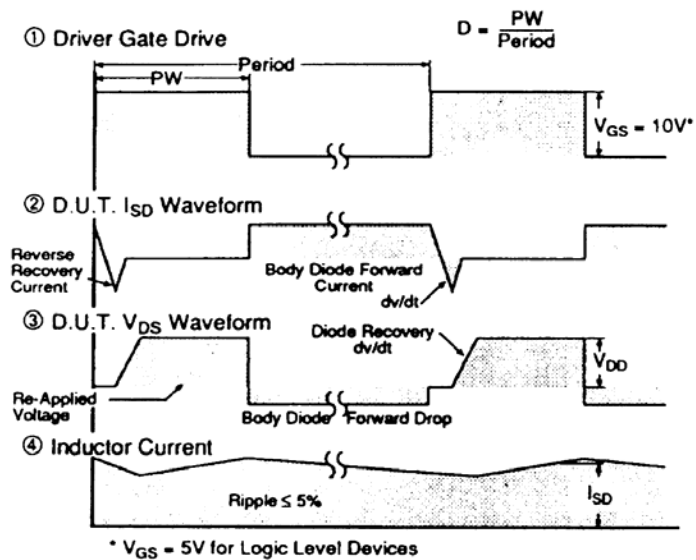
Fig 13b. Gate Charge Test Circuit

**dv/dt Test Circuit**

**Fig 14.** For N-Channel HEXFETs



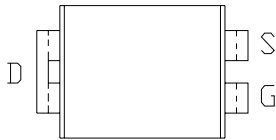
**Peak Diode Recovery Test Circuit**



# IRFD420PbF

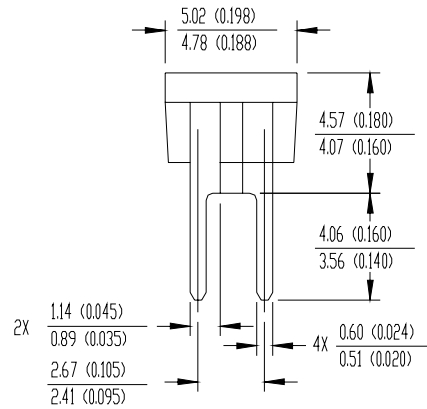
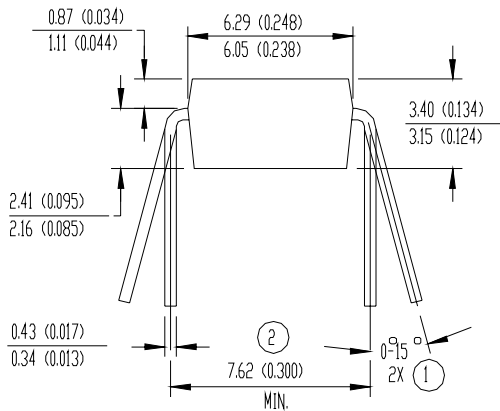
## Hexdip Package Outline

Dimensions are shown in millimeters (inches)



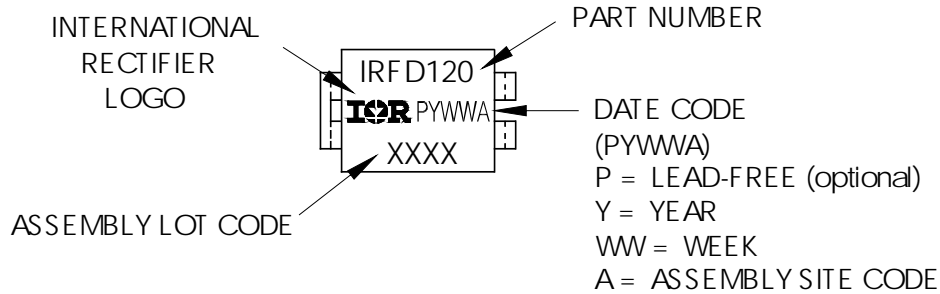
NOTES:

- ① APPLIES TO SPREAD OF LEADS PRIOR TO INSTALLATION
- ② APPLIES TO INSTALLED LEAD CENTERS
- 3 CONTROLLING DIMENSION: INCH.
- 4 DIMENSIONS ARE SHOWN MILLIMETERS (INCHES).
- 5 CASE STYLE HD-1 (SIMILAR TO JEDEC OUTLINE MO-001AN)
- 6 DIMENSIONS SHOWN ARE BEFORE SOLDER DIP  
SOLDER DIP MAX. + 0.16 (0.006)



## Hexdip Part Marking Information

EXAMPLE: THIS IS AN IRFD120



Data and specifications subject to change without notice.



IR WORLD HEADQUARTERS: 233 Kansas St., El Segundo, California 90245, USA Tel: (310) 252-7105  
TAC Fax: (310) 252-7903  
10/04





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